



N-channel Enhancement-mode Power MOSFET

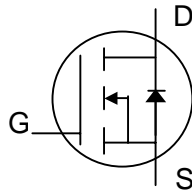
Simple Drive Requirement

Industry Standard Compatible "5x6"

Package with Heatsink

Low On-resistance

RoHS-compliant, halogen-free

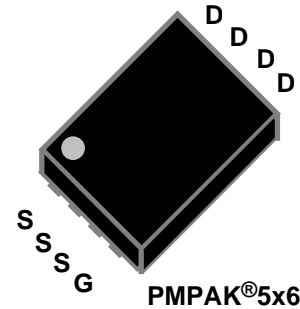


| | |
|--------------|-------|
| BV_{DSS} | 75V |
| $R_{DS(ON)}$ | 7.5mΩ |
| I_D | 65A |

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The PMPAK[®]5x6 package is specially designed for DC-DC converter applications, with a foot print that is compatible with other popular "5x6" packages and offers a backside heat sink and low package profile.



Absolute Maximum Ratings

| Symbol | Parameter | Rating | Units |
|---------------------------------|--|------------|-------|
| V_{DS} | Drain-Source Voltage | 75 | V |
| V_{GS} | Gate-Source Voltage | ±20 | V |
| I_D at $T_C=25^\circ\text{C}$ | Continuous Drain Current (Chip) | 65 | A |
| I_D at $T_A=25^\circ\text{C}$ | Continuous Drain Current ³ | 18.4 | A |
| I_D at $T_A=70^\circ\text{C}$ | Continuous Drain Current ³ | 14.7 | A |
| I_{DM} | Pulsed Drain Current ¹ | 200 | A |
| P_D at $T_C=25^\circ\text{C}$ | Total Power Dissipation | 62.5 | W |
| P_D at $T_A=25^\circ\text{C}$ | Total Power Dissipation | 5 | W |
| E_{AS} | Single Pulse Avalanche Energy ⁴ | 28.8 | mJ |
| T_{STG} | Storage Temperature Range | -55 to 150 | °C |
| T_J | Operating Junction Temperature Range | -55 to 150 | °C |

Thermal Data

| Symbol | Parameter | Value | Units |
|--------|---|-------|-------|
| Rthj-c | Maximum Thermal Resistance, Junction-case | 2.0 | °C/W |
| Rthj-a | Maximum Thermal Resistance, Junction-ambient ³ | 25 | °C/W |

Ordering Information

AP94T07GMT-HF-3TR

RoHS-compliant halogen-free PMPAK[®]5x6, shipped on tape and reel (3000pcs/reel)

PMPAK[®] is a registered trademark of Advanced Power Electronics Corp.



Electrical Specifications at $T_j=25^\circ\text{C}$ (unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|--------------|--|-------------------------------|------|------|-----------|------------|
| BV_{DSS} | Drain-Source Breakdown Voltage | $V_{GS}=0V, I_D=250\mu A$ | 75 | - | - | V |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance ² | $V_{GS}=10V, I_D=30A$ | - | - | 7.5 | m Ω |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}=V_{GS}, I_D=250\mu A$ | 2 | - | 5 | V |
| g_{fs} | Forward Transconductance | $V_{DS}=10V, I_D=30A$ | - | 55 | - | S |
| I_{DSS} | Drain-Source Leakage Current | $V_{DS}=60V, V_{GS}=0V$ | - | - | 25 | μA |
| I_{GSS} | Gate-Source Leakage | $V_{GS}=\pm 20V$ | - | - | ± 100 | nA |
| Q_g | Total Gate Charge ² | $I_D=30A$ | - | 54 | 86 | nC |
| Q_{gs} | Gate-Source Charge | $V_{DS}=40V$ | - | 14.5 | - | nC |
| Q_{gd} | Gate-Drain ("Miller") Charge | $V_{GS}=10V$ | - | 25 | - | nC |
| $t_{d(on)}$ | Turn-on Delay Time ² | $V_{DS}=40V$ | - | 16 | - | ns |
| t_r | Rise Time | $I_D=1A$ | - | 14 | - | ns |
| $t_{d(off)}$ | Turn-off Delay Time | $R_G=3.3\Omega, V_{GS}=10V$ | - | 40 | - | ns |
| t_f | Fall Time | $R_D=40\Omega$ | - | 37 | - | ns |
| C_{iss} | Input Capacitance | $V_{GS}=0V$ | - | 2350 | 3760 | pF |
| C_{oss} | Output Capacitance | $V_{DS}=25V$ | - | 390 | - | pF |
| C_{rss} | Reverse Transfer Capacitance | $f=1.0\text{MHz}$ | - | 245 | - | pF |
| R_g | Gate Resistance | $f=1.0\text{MHz}$ | - | 1.3 | - | Ω |

Source-Drain Diode

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|----------|------------------------------------|-----------------------|------|------|------|-------|
| V_{SD} | Forward On Voltage ² | $I_S=30A, V_{GS}=0V$ | - | - | 1.3 | V |
| t_{rr} | Reverse Recovery Time ² | $I_S=10A, V_{GS}=0V,$ | - | 46 | - | ns |
| Q_{rr} | Reverse Recovery Charge | $di/dt=100A/\mu s$ | - | 86 | - | nC |

Notes:

1. Pulse width limited by maximum junction temperature
2. Pulse test
3. Surface mounted on 1 in² copper pad of FR4 board, $t \leq 10\text{sec}$, 60°C/W at steady state.
4. Starting $T_j=25^\circ\text{C}$, $V_{DD}=30V$, $L=0.1\text{mH}$, $R_G=25\Omega$, $I_{AS}=24A$.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

APEC RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN.



Typical Electrical Characteristics

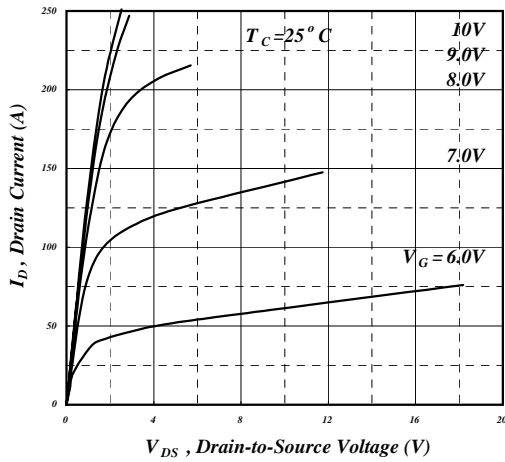


Fig 1. Typical Output Characteristics

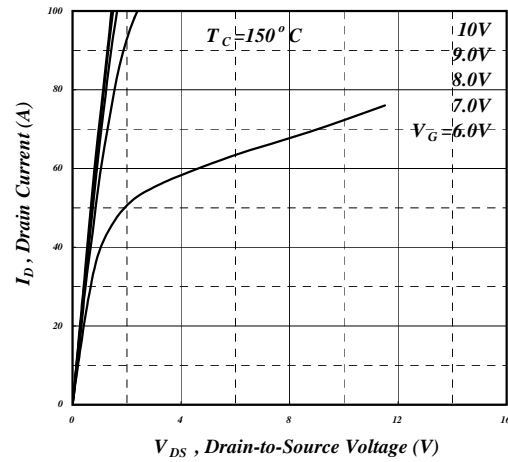


Fig 2. Typical Output Characteristics

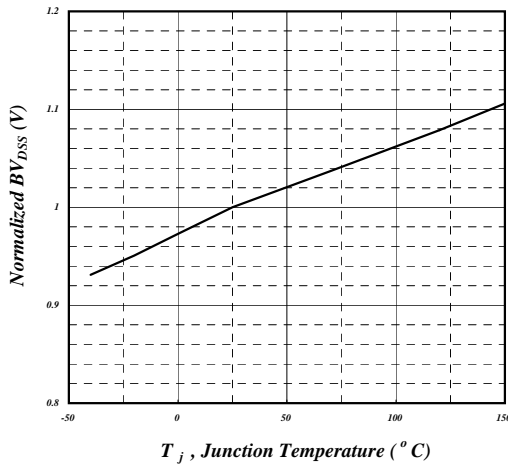


Fig 3. Normalized BVDSS vs. Junction Temperature

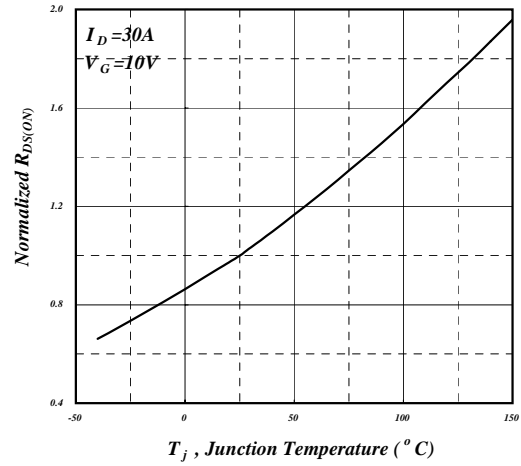


Fig 4. Normalized On-Resistance vs. Junction Temperature

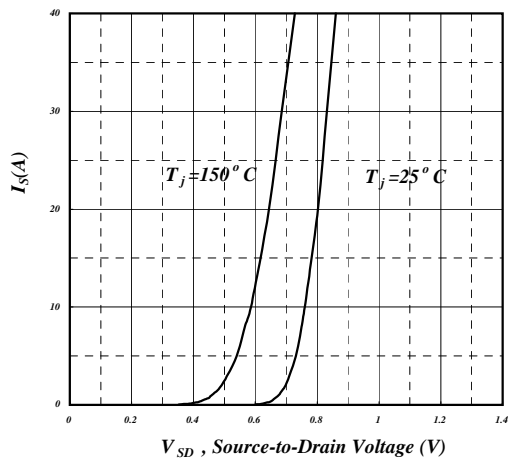


Fig 5. Forward Characteristic of Reverse Diode

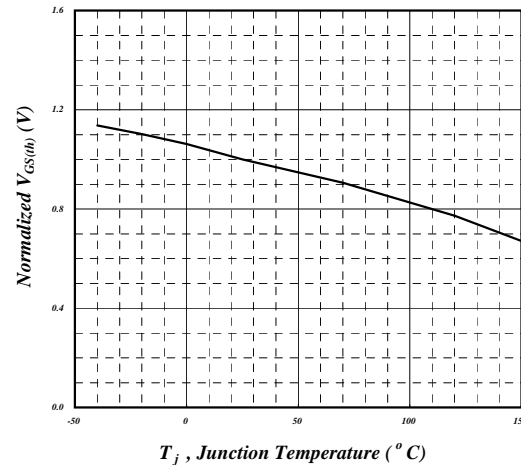


Fig 6. Gate Threshold Voltage vs. Junction Temperature



Typical Electrical Characteristics (cont.)

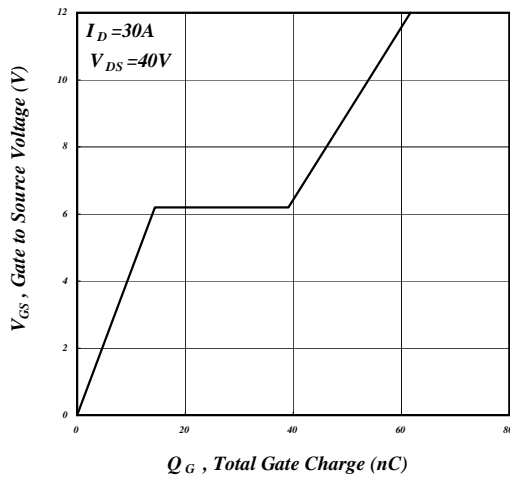


Fig 7. Gate Charge Characteristics

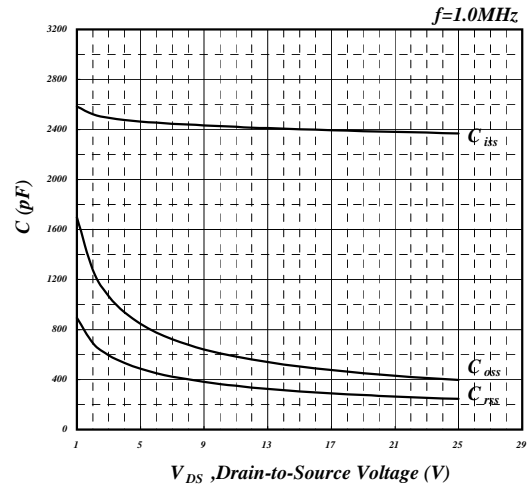


Fig 8. Typical Capacitance Characteristics

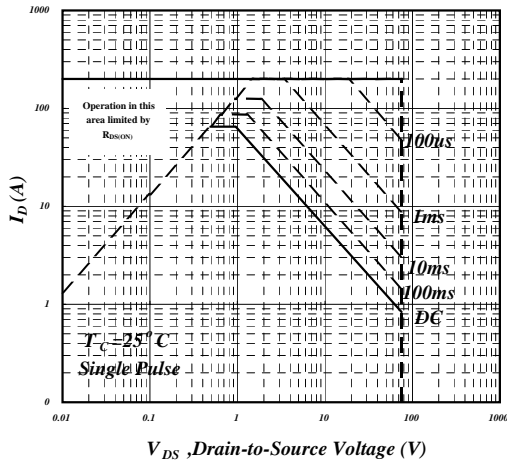


Fig 9. Maximum Safe Operating Area

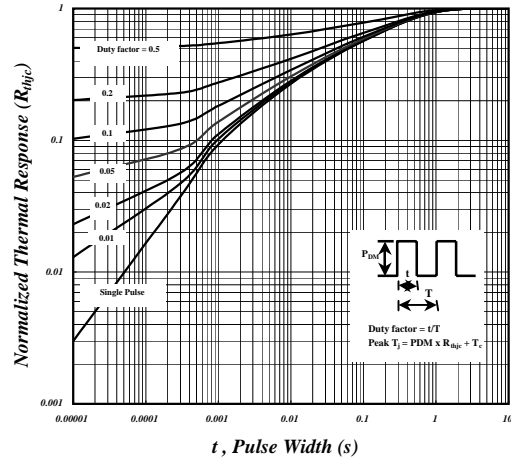


Fig 10. Effective Transient Thermal Impedance

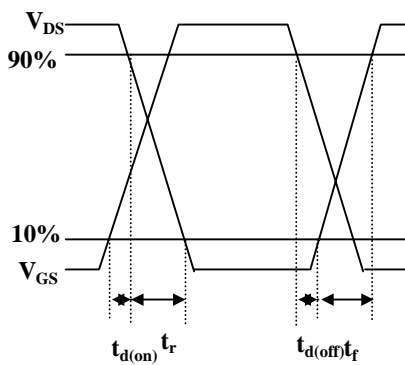


Fig 11. Switching Time Waveforms

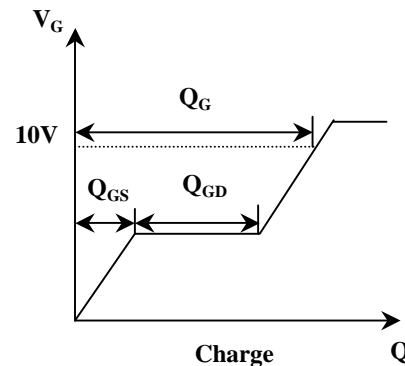
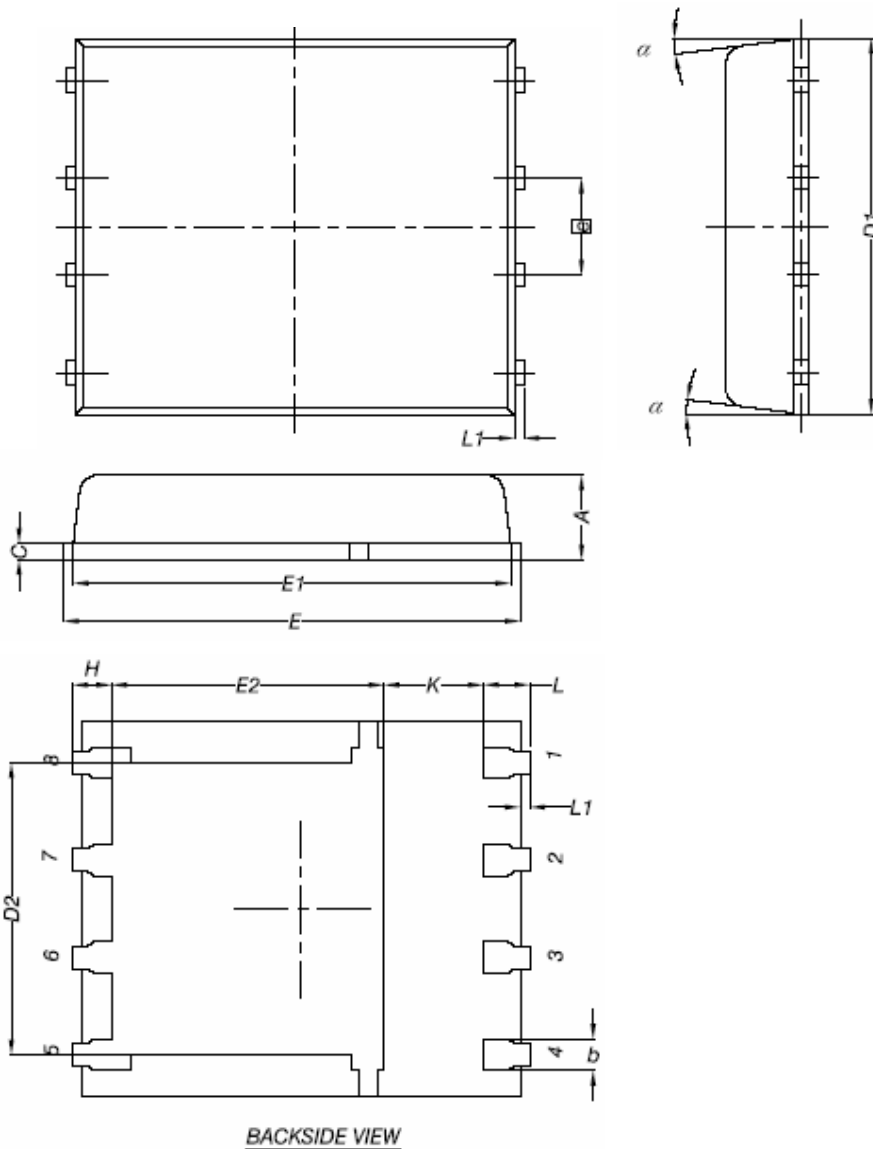


Fig 12. Gate Charge Waveform



Package Dimensions: PMPAK[®]5x6



| SYMBOLS | Millimeters | | |
|----------------|-------------|------|------|
| | MIN | NOM | MAX |
| A | 0.90 | 1.00 | 1.10 |
| b | 0.33 | 0.41 | 0.51 |
| C | 0.20 | - | - |
| D1 | 4.80 | 4.90 | 5.10 |
| D2 | - | - | 4.20 |
| E | 5.90 | 6.00 | 6.10 |
| E1 (Reference) | 5.70 | 5.75 | 5.80 |
| E2 (Reference) | 3.38 | 3.58 | 3.78 |
| e | 1.27 BSC | | |
| H | - | - | 0.62 |
| K (Reference) | 0.70 | - | - |
| L | 0.51 | 0.61 | 0.71 |
| L1 | - | - | 0.20 |
| α(Reference) | 0° | - | 12° |

1. All dimensions are in millimeters.
2. Dimensions do not include mold protrusions.

Marking Information:

